



2SB435

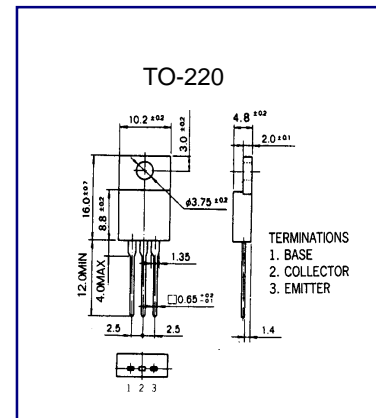
PNP EPITAXIAL SILICON TRANSISTOR

LOW FREQUENCY POWER AMPLIFIER

- Complement to 2SD235

ABSOLUTE MAXIMUM RATINGS ($T_A=25^\circ\text{C}$)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V _{CB0}	-50	V
Collector-Emitter Voltage	V _{CE0}	-40	V
Emitter-Base voltage	V _{EB0}	-5	V
Collector Current (DC)	I _C	-3	A
Collector Dissipation ($T_c=25^\circ\text{C}$)	P _C	25	W
Junction Temperature	T _j	150	°C
Storage Temperature	T _{stg}	-50~150	°C



ELECTRICAL CHARACTERISTICS ($T_A=25^\circ\text{C}$)

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
Collector Cutoff Current	I _{CBO}	V _{CB} = -50V, I _E = 0			-10	μA
Emitter Cutoff Current	I _{EB0}	V _{EB} = -5V, I _C = 0			10	μA
DC Current Gain	h _{FE1}	V _{CE} = -5V, I _C = -0.5A	40		240	
Collector- Emitter Saturation Voltage	V _{CE(sat)}	I _C = -3A, I _B = -0.3A			-1.0	V
Current Gain Bandwidth Product	f _T	V _{CE} = -2V, I _C = -0.5A		18		MHZ